## Features

- Positive Voltage Control ( $0 /+5 \mathrm{~V}$ )
- High Isolation: $54 \mathrm{~dB} @ 0.9 \mathrm{GHz}$

52 dB @ 1.9 GHz

- 50-Ohm Internal Terminations
- Low Insertion Loss: $0.6 \mathrm{~dB} @ 0.9 \mathrm{GHz}$ 0.7 dB @ 1.9 GHz
- 4 mm 16-Lead PQFN Package


## Description

The SW-475 GaAs monolithic switch provides high isolation in a low-cost, plastic surface mount package. The SW-475 is ideal for applications across a broad range of frequencies including synthesizer switching, transmit / receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCS, GPS, and fiber optic modules.

The SW-475 is fabricated using M/A-COM Technology Solutions' 1.0-micron gate length MESFET process. The process features full chip passivation for performance and reliability.

## Ordering Information ${ }^{1}$

| Part Number | Package |
| :---: | :---: |
| SW-475 PIN | Bulk Packaging |
| SW-475TR | 1000 piece reel |
| SW-475TR-3000 | 3000 piece reel |
| SW-475SMB | Sample board |

1. Reference Application Note M513 for reel size information.

## Functional Schematic



## PIN Configuration

| Pin | Function | Description |
| :---: | :---: | :---: |
| 1 | RF2 | RF port |
| 2 | GND | RF ground |
| 3 | GND | RF ground |
| 4 | V1 | Control 1 |
| 5 | V2 | Control 2 |
| 6 | GND | RF ground |
| 7 | RFC | RF port |
| 8 | GND | RF ground |
| 9 | GND | RF ground |
| 10 | GND | RF ground |
| 11 | GND | RF ground |
| 12 | RF1 | RF port |
| 13 | GND | RF ground |
| 14 | GND | RF ground |
| 15 | GND | RF ground |
| 16 | GND | RF ground |
| 17 (pad) | GND | RF ground |

2. The exposed pad centered on the package bottom must be connected to RF and DC ground.

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## Electrical Specifications ${ }^{3}$ : $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CTL}}=0,5.0 \mathrm{~V}$ (unless otherwise specified)

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Insertion Loss | $\begin{gathered} 0.5-1 \mathrm{GHz} \\ 1.0-2.0 \mathrm{GHz} \\ 2.0-3.0 \mathrm{GHz} \end{gathered}$ | dB | - | $\begin{gathered} 0.6 \\ 0.7 \\ 0.75 \end{gathered}$ | $\begin{aligned} & 0.7 \\ & 0.8 \\ & 0.9 \end{aligned}$ |
| Isolation | $\begin{gathered} 0.5-1 \mathrm{GHz} \\ 1.0-2.0 \mathrm{GHz} \\ 2.0-3.0 \mathrm{GHz} \end{gathered}$ | dB | $\begin{aligned} & 51 \\ & 48 \\ & 45 \end{aligned}$ | $\begin{aligned} & 54 \\ & 52 \\ & 50 \end{aligned}$ | - |
| Return Loss | $\begin{gathered} 0.5-1 \mathrm{GHz} \\ 1.0-2.0 \mathrm{GHz} \\ 2.0-3.0 \mathrm{GHz} \end{gathered}$ | dB | $\begin{aligned} & 15 \\ & 15 \\ & 15 \end{aligned}$ | $\begin{aligned} & 20 \\ & 20 \\ & 20 \end{aligned}$ | - |
| Input IP2 | 2-Tone 900 MHz , 5 MHz spacing ( $\mathrm{V}_{\mathrm{C}}=5.0 \mathrm{~V}$ ) | dBm | - | 83 | - |
| Input IP3 | 2-Tone $900 \mathrm{MHz}, 5 \mathrm{MHz}$ spacing ( $\mathrm{V}_{\mathrm{C}}=5.0 \mathrm{~V}$ ) | dBm | - | 46 | - |
| P1dB | $\begin{aligned} & 1 \mathrm{GHz}, 5 \mathrm{~V} \\ & 1 \mathrm{GHz}, 3 \mathrm{~V} \end{aligned}$ | dBm | - | $\begin{aligned} & 27 \\ & 18 \end{aligned}$ | - |
| P0.1dB | $\begin{aligned} & 1 \mathrm{GHz}, 5 \mathrm{~V} \\ & 1 \mathrm{GHz}, 3 \mathrm{~V} \end{aligned}$ | dBm | - | $\begin{aligned} & 24 \\ & 11 \end{aligned}$ |  |
| $\mathrm{T}_{\text {RISE }}, \mathrm{T}_{\text {FALL }}$ | 10\% to $90 \%$ RF \& $90 \%$ to $10 \%$ RF | ns | - | 24 | - |
| Ton, ${ }_{\text {OfF }}$ | $50 \%$ of $\mathrm{V}_{\mathrm{c}}$ to $10 \% / 90 \% \mathrm{RF}$ | ns | - | 15 | - |
| Transients | $\mathrm{V}_{\mathrm{C}}=5.0 \mathrm{~V}$ square wave, in-band | mV | - | 12 | - |
| Control Current | $\left\|\mathrm{V}_{\mathrm{C}}\right\|=4.5 \mathrm{~V}, 0 \mathrm{dBm}$ | $\mu \mathrm{A}$ | - | 2 | 13 |

3. DC blocking capacitors requires on all RF ports.

## Absolute Maximum Ratings ${ }^{4,5}$

| Parameter | Absolute Maximum |
| :---: | :---: |
| Input Power $(0.5-3.0 \mathrm{GHz})$ <br> 3 V Control <br> 5 V Control | +30 dBm <br> +33 dBm |
| Operating Voltage | +8.5 volts |
| Operating Temperature | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Storage Temperature | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |

4. Exceeding any one or combination of these limits may cause permanent damage to this device.
5. $\mathrm{M} / \mathrm{A}-\mathrm{COM}$ does not recommend sustained operation near these survivability limits.

## Truth Table ${ }^{6}$

| V1 | V2 | RFC - RF1 | RFC - RF2 |
| :---: | :---: | :---: | :---: |
| 0 | 1 | ON | OFF |
| 1 | 0 | OFF | ON |

6. External DC blocking capacitors required on all RF ports. We recommend 47 pF .

| Logic Level | Voltage Level |
| :---: | :---: |
| 0 | $0 \mathrm{~V} \pm 0.2 \mathrm{~V}$ |
| 1 | 3.0 V to 8.0 V |

## Typical Performance Curves

Return Loss Vs. Frequency


Isolation Vs. Frequency Over Temperature


Insertion Loss Vs. Temperature


## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

## 4 mm 16-Lead PQFN

